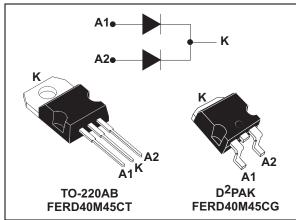


FERD40M45C

Field effect rectifier

Datasheet - production data



I_{F(AV)}

Description

for a given silicon surface.

2 x 20 A 45 V V_{RRM} V_F(typ) 0.34 V

Table 1. Device summary

Packaged in TO-220AB, and D²PAK, this device is intended to be used in switch mode power

This dual rectifier is based on a proprietary technology that achieves the best in class V_F/I_R

supplies, or automotive applications

Features

- ST advanced rectifier process
- Stable leakage current over reverse voltage
- Low forward voltage drop
- High frequency operation

Characteristics FERD40M45C

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode at 25° C, unless otherwise stated)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			45	V
I _{F(RMS)}	Forward rms current			40	Α
I _{F(AV)}	Average forward current, $\delta = 0.5$	T _c =150° C T _c =140° C	Per diode Per device	20 40	Α
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoi	t _p = 10 ms sinusoidal		
T _{stg}	Storage temperature range			-65 to + 175	°C
	Maximum operating junction	TO-220AB, D ² PAK		175	
T _j	Maximum operating junction temperature (1)	D ² PAK (DC forward current without reverse bias, t = 1 hour)		200	°C

^{1.} $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistances

Symbol	Parameter	Value	Unit	
R _{th (j-c)}	Junction to case	Per diode otal	1.6 1.1	°C/W
R _{th(c)}	Coupling		0.5	°C/W

When the diodes 1 and 2 are used simultaneously:

 $\Delta T_j(\text{diode 1}) = P(\text{diode1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode2}) \times R_{th(c)}.$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
{I} (1)	$I_R^{(1)}$ Reverse leakage current $ \frac{T_j = 25^{\circ} \text{ C}}{T_j = 125^{\circ} \text{ C}} $ $V_R = V_{RRM}$			650	μΑ		
'R`		T _j = 125° C	VR = VRRM		25	50	mA
V _F ⁽²⁾	Forward voltage drop $T_{j} = 125^{\circ} C$ $T_{i} = 25^{\circ} C$	T _j = 25° C	I _F = 10 A		0.38	0.415	V
		T _j = 125° C			0.34	0.37	
		T _j = 25° C	1 20 4		0.46	0.50	V
		I _F = 20 A		0.46	0.50		

^{1.} Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.31 \text{ x } I_{F(AV)} + 0.0095 I_{F}^{2}_{(RMS)}$$

^{2.} Pulse test: $t_p = 380 \mu s$, $\delta < 2\%$

FERD40M45C Characteristics

Figure 1. Average forward power dissipation versus average forward current (per diode)

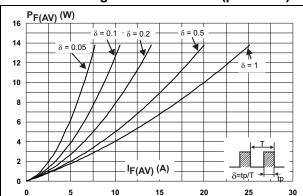


Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$, per diode)

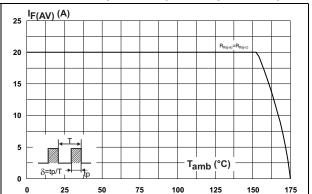
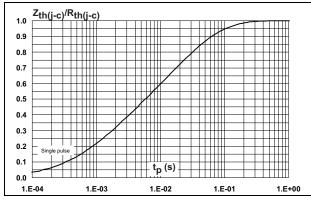


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Reverse leakage current versus reverse voltage applied (typical values, per diode)



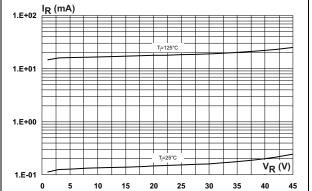
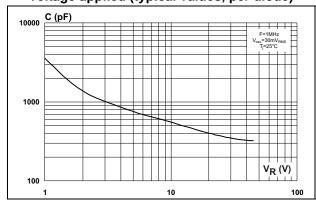
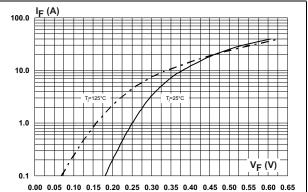


Figure 5. Junction capacitance versus reverse voltage applied (typical values, per diode)

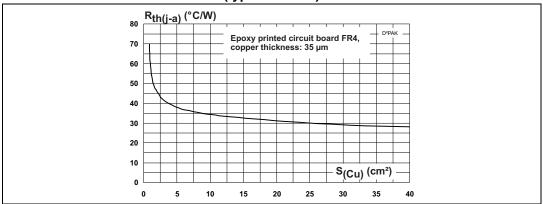
Figure 6. Forward voltage drop versus forward current (typical values, per diode)





Characteristics FERD40M45C

Figure 7. Thermal resistance junction to ambient versus copper surface under tab (typical values)



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2 Package Information

- Epoxy meets UL94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N⋅m (TO-220AB)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Resin gate
0.5 mm max,
protrusion(1)

Resin gate
0.5 mm max,
protrusion(1)

Resin gate
0.5 mm max,
protrusion(1)

(1) Resin gate position accepted in each of the two position shown as well as the symmetrical opposites

Figure 8. TO-220AB dimension definitions

Package Information FERD40M45C

Table 5. TO-220AB dimension values

	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.17	0.18	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.045	0.067	
С	0.48	0.70	0.019	0.027	
D	15.25	15.75	0.60	0.62	
D1	1.27 typ.		0.05 typ.		
E	10	10.40	0.39	0.41	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.19	0.20	
F	1.23	1.32	0.048	0.052	
H1	6.20	6.60	0.24	0.26	
J1	2.40	2.72	0.094	0.107	
L	13	14	0.51	0.55	
L1	3.50	3.93	0.137	0.154	
L20	16.40 typ.		0.64 typ.		
L30	28.90 typ.		1.13 typ.		
ØP	3.75	3.85	0.147	0.151	
Q	2.65	2.95	0.104	0.116	

FERD40M45C Package Information

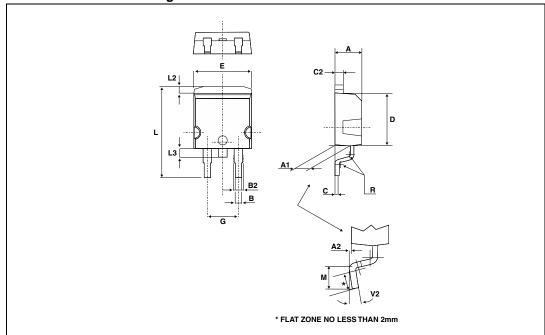


Figure 9. D²PAK dimension definitions

Table 6. D²PAK dimension values

	Dimensions					
Ref.	Millimeters		Inches			
	Min.	Max.	Min.	Max.		
Α	4.40	4.60	0.173	0.181		
A1	2.49	2.69	0.098	0.106		
A2	0.03	0.23	0.001	0.009		
В	0.70	0.93	0.027	0.037		
B2	1.14	1.70	0.045	0.067		
С	0.45	0.60	0.017	0.024		
C2	1.23	1.36	0.048	0.054		
D	8.95	9.35	0.352	0.368		
E	10.00	10.40	0.393	0.409		
G	4.88	5.28	0.192	0.208		
L	15.00	15.85	0.590	0.624		
L2	1.27	1.40	0.050	0.055		
L3	1.30	1.75	0.051	0.069		
М	2.29	2.79	0.090	0.110		
R	0.40 typ.		0.016 typ.			
V2	0°	8°	0°	8°		



Package Information FERD40M45C

16.90

12.2

16.90

2.54

3.50

9.75

Figure 10. D²PAK footprint (dimensions in mm)



3 Ordering Information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
FERD40M45CT	FERD40M45CT	TO-220AB	2.2 g	50	Tube
FERD40M45CG-TR	FERD40M45CG	D ² PAK	1.8 g	500	Tape and reel

4 Revision history

Table 8. Document revision history

Date	Revision	Description of Changes
13-Nov-2013	1	Initial release



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